

Electronic Supplementary Information

Enhanced light out-coupling efficiency of quantum dot light emitting diodes by nanoimprint lithography

Shujie Wang,^a Xiaoyu Dou,^a Ling Chen,^a Yan Fang,^a Aqiang Wang,^a Huaibin Shen,^a Zuliang Du^{*a}

Key Lab for Special Functional Materials of Ministry of Education, Collaborative Innovation Center of Nano Functional Materials and Applications, Henan University, Kaifeng, 475004, People's Republic of China.

Email: zld@henu.edu.cn

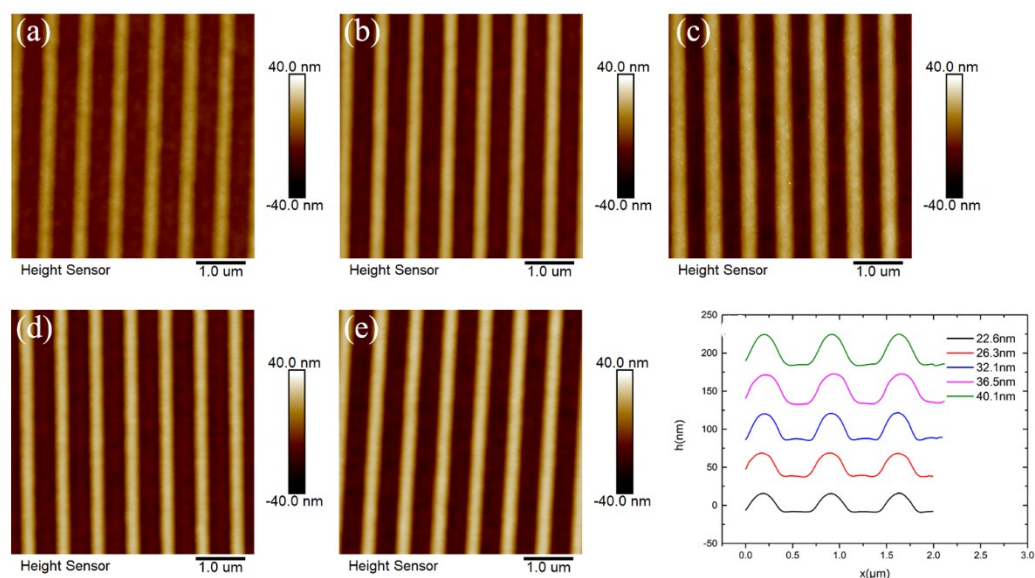


Figure S1. The AFM images of different height of PEDOT:PSS layers. (a)22.6nm (b)26.3nm (c)32.1nm (d)36.5nm (e)40.1nm (f) Section analysis of PEDOT:PSS layers.

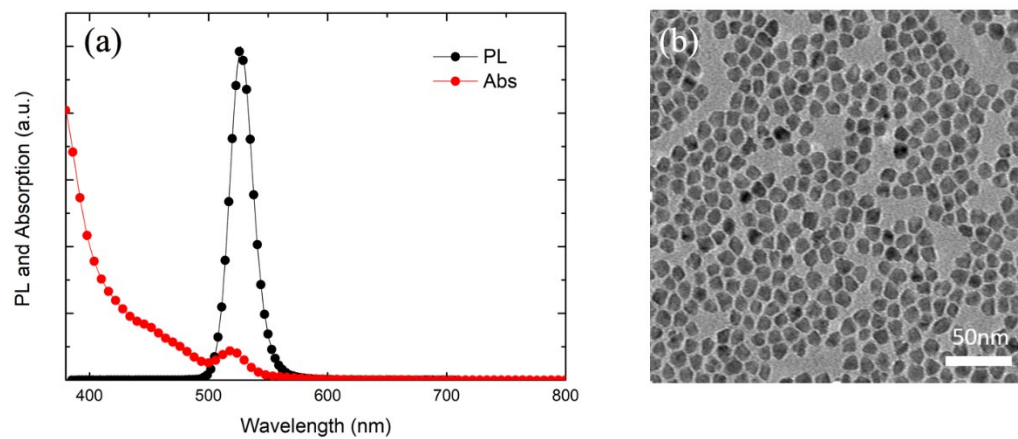


Figure S2. (a) The absorption and PL spectrum of QDs. (b) TEM image of QDs used in this work.

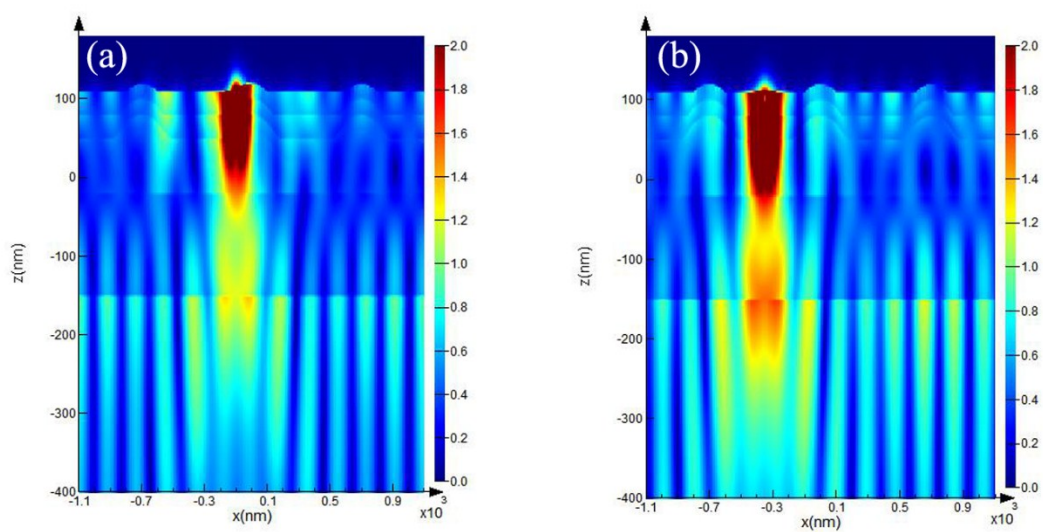


Figure S3. Calculated distribution of the power field intensity in the QLEDs with different location of dipole at slope (a) and valley (b) of grating PEDOT:PSS layers at the wavelength of 525 nm.